2SC4807

Silicon NPN Epitaxial

REJ03G0731-0300
(Previous ADE-208-1122A)
Rev.3.00
Aug.10.2005

Application

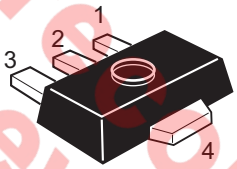
VHF / UHF wide band amplifier

Features

- High gain bandwidth product
  f_T = 4.4 GHz Typ
- High output power
  1 dB Power compression point Pcp = 24 dBm Typ at V_{CE} = 5V , I_C = 100 mA , f = 900 MHz

Outline

RENESAS Package code: PLZZ0004CA-A
(Package name: UPAK®)



1. Base
2. Collector
3. Emitter
4. Collector (Flange)

Note: Marking is “ER”.

*UPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	15	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	200	mA
Collector power dissipation	P_C*[1]	800	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Note: 1. Value on the alumina ceramics board (12.5 x 20 x 0.7 mm)

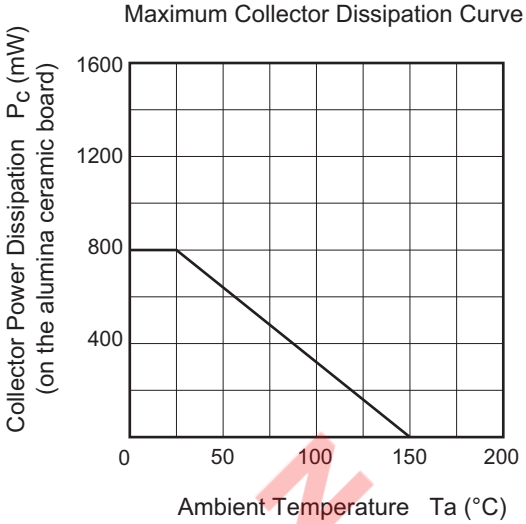
Electrical Characteristics

(Ta = 25°C)

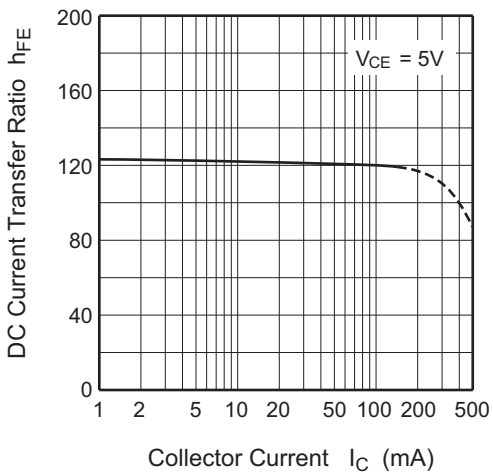
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	30	—	V	I_C = 10 µA, I_E = 0
Collector cutoff current	I_{CBO}	—	—	1	µA	V_{CB} = 15 V, I_E = 0
	I_{CEO}	—	—	1	mA	V_{CE} = 15 V, R_{BE} = ∞
Emitter cutoff current	I_{EBO}	—	—	10	µA	V_{EB} = 2 V, I_C = 0
DC current transfer ratio	h_{FE}	50	120	250		V_{CE} = 5 V, I_C = 100 mA
Collector output capacitance	Cob	—	2.8	4.0	pF	V_{CB} = 5 V, I_E = 0, f = 1 MHz
Gain bandwidth product	f_T	3.0	4.4	—	GHz	V_{CE} = 5 V, I_C = 100 mA
Power gain	PG	5.0	7.0	—	dB	V_{CE} = 5 V, I_C = 100 mA, f = 900 MHz
Noise figure	NF	—	2.5	4.0	dB	V_{CE} = 5 V, I_C = 20 mA, f = 900 MHz

Main Characteristics

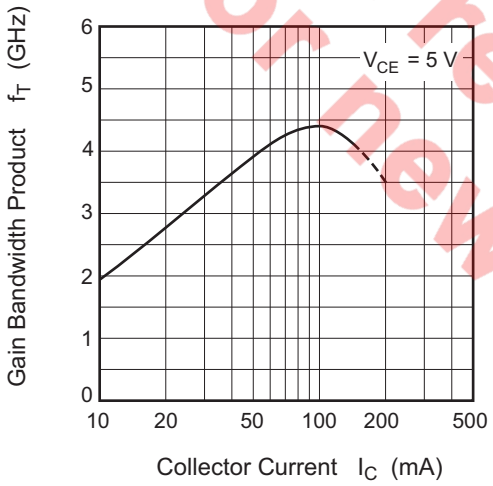
Maximum Collector Dissipation Curve



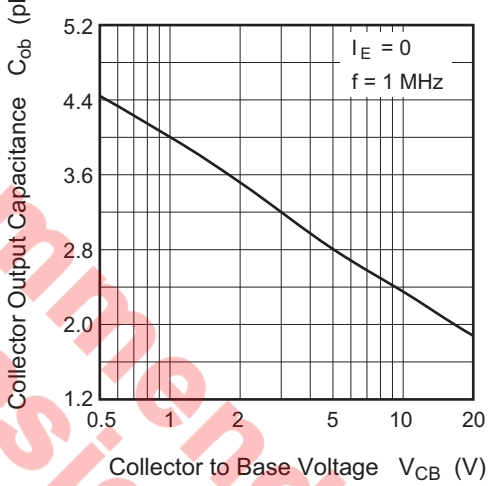
DC Current Transfer Ratio vs. Collector Current



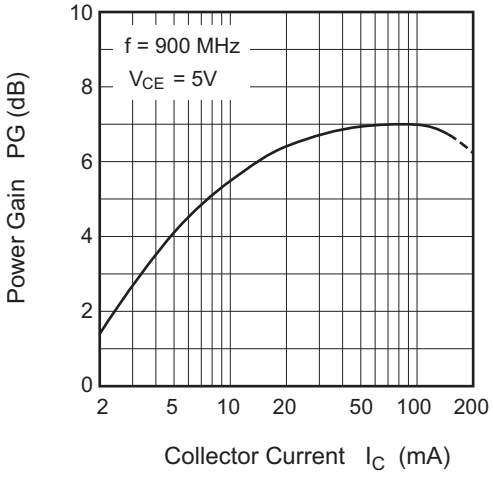
Gain Bandwidth Product vs. Collector Current



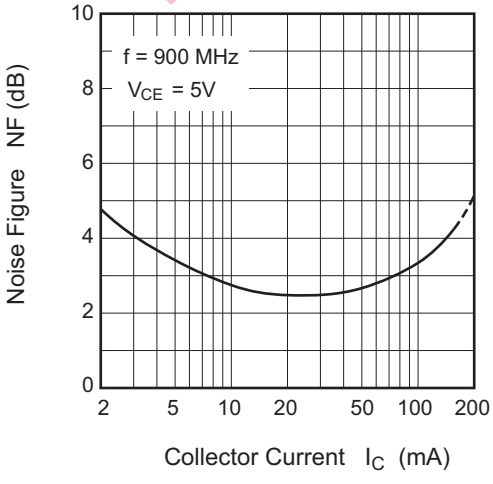
Collector Output Capacitance vs. Collector to Base Voltage



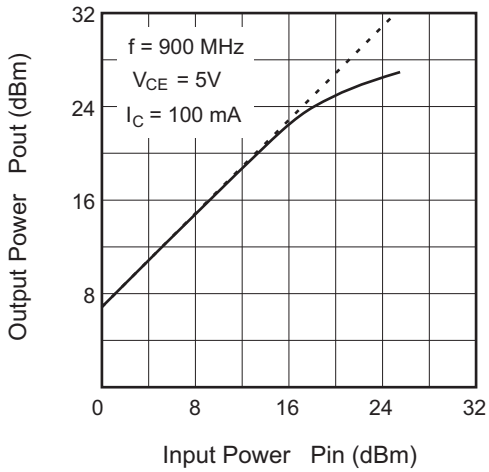
Power Gain vs. Collector Current



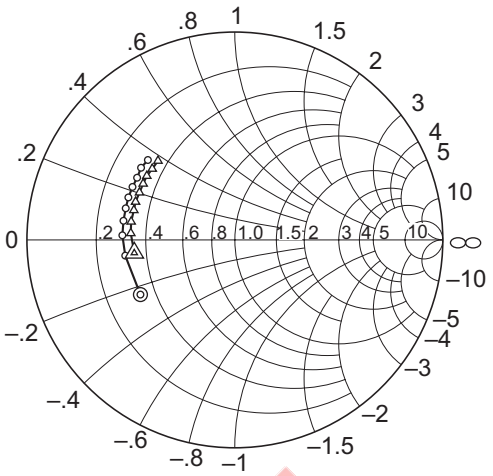
Noise Figure vs. Collector Current



Output Power vs. Input Power

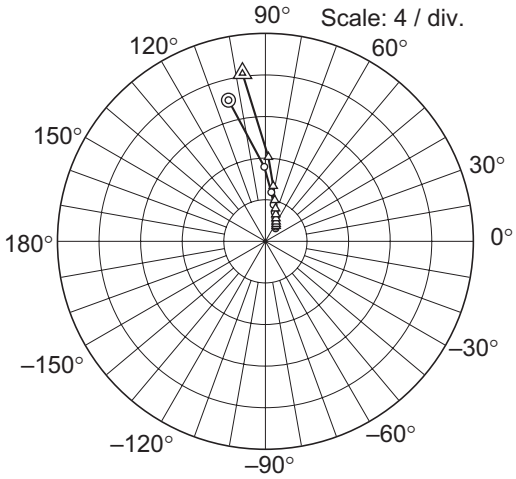


S11 Parameter vs. Frequency



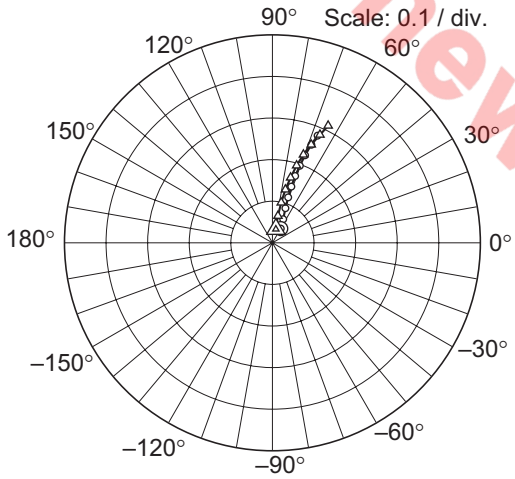
Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 MHz (100 MHz step)
(I_C = 20 mA)
(I_C = 100 mA)

S21 Parameter vs. Frequency



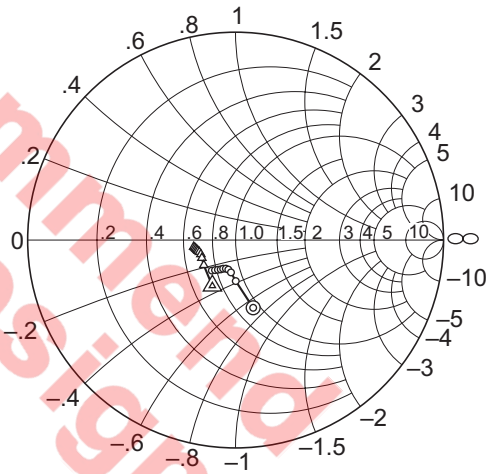
Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 MHz (100 MHz step)
(I_C = 20 mA)
(I_C = 100 mA)

S12 Parameter vs. Frequency



Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 MHz (100 MHz step)
(I_C = 20 mA)
(I_C = 100 mA)

S22 Parameter vs. Frequency



Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 MHz (100 MHz step)
(I_C = 20 mA)
(I_C = 100 mA)

S Parameter

(V_{CE} = 5 V, I_C = 20 mA, Z_O = 50 Ω, Emitter Common)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100	0.525	–150.0	14.03	104.7	0.039	58.4	0.336	–75.5
200	0.533	–171.9	7.16	90.9	0.063	65.7	0.197	–89.9
300	0.542	177.6	4.75	83.2	0.089	69.6	0.157	–98.3
400	0.544	170.2	3.60	77.5	0.116	71.0	0.146	–104.0
500	0.547	163.8	2.91	72.1	0.143	71.5	0.145	–109.0
600	0.552	158.2	2.46	67.4	0.170	71.3	0.150	–113.7
700	0.555	152.6	2.14	63.3	0.197	70.5	0.158	–117.1
800	0.558	147.5	1.90	59.3	0.225	69.6	0.166	–121.0
900	0.570	142.4	1.72	55.2	0.254	68.4	0.175	–124.6
1000	0.569	137.4	1.58	51.9	0.280	67.2	0.186	–128.1

S Parameter

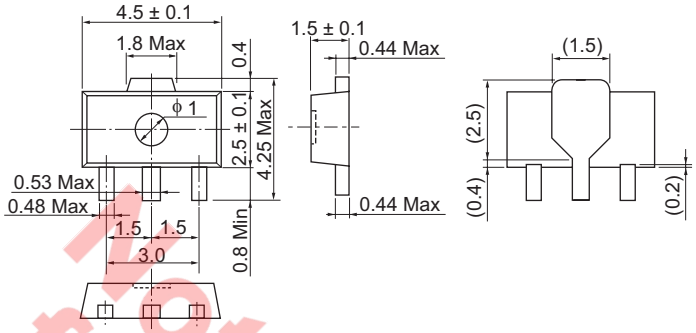
(V_{CE} = 5 V, I_C = 100 mA, Z_O = 50 Ω, Emitter Common)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100	0.488	–172.8	16.32	97.8	0.034	76.2	0.248	–116.9
200	0.502	176.3	8.08	88.0	0.066	78.6	0.195	–141.9
300	0.507	170.0	5.34	82.0	0.099	77.8	0.184	–152.2
400	0.507	163.6	4.03	77.2	0.132	76.4	0.181	–157.9
500	0.514	159.0	3.27	72.8	0.163	74.5	0.184	–161.8
600	0.513	153.6	2.75	68.8	0.195	72.7	0.189	–164.0
700	0.518	148.5	2.40	65.1	0.225	70.7	0.192	–165.8
800	0.524	144.0	2.13	61.3	0.254	68.5	0.196	–167.6
900	0.525	139.3	1.93	57.8	0.284	66.3	0.200	–169.4
1000	0.531	134.2	1.77	54.6	0.312	64.6	0.205	–170.8

Package Dimensions

JEITA Package Code	RENESAS Code	Package Name	MASS[Typ.]
SC-62	PLZZ0004CA-A	UPAK / UPAKV	0.050g

Unit: mm



Ordering Information

Part Name	Quantity	Shipping Container
2SC4807ERTR-E	1000	φ 178 mm Reel, 8 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

RENESAS SALES OFFICES

http://www.renesas.com

Refer to "**http://www.renesas.com/en/network**" for the latest and detailed information.

Renesas Technology America, Inc.
450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.
10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.
Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.
Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510

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